

EE 320 Electronics

2/22/13 Lecture 9

2.45 & 2.51

2.45 p-type $1 \Omega \cdot \text{cm}$
boron impurities (acceptor)

$$1 \Omega \cdot \text{cm} = \rho \approx \frac{1}{q \cdot \mu_p \cdot N_{Ai}}$$

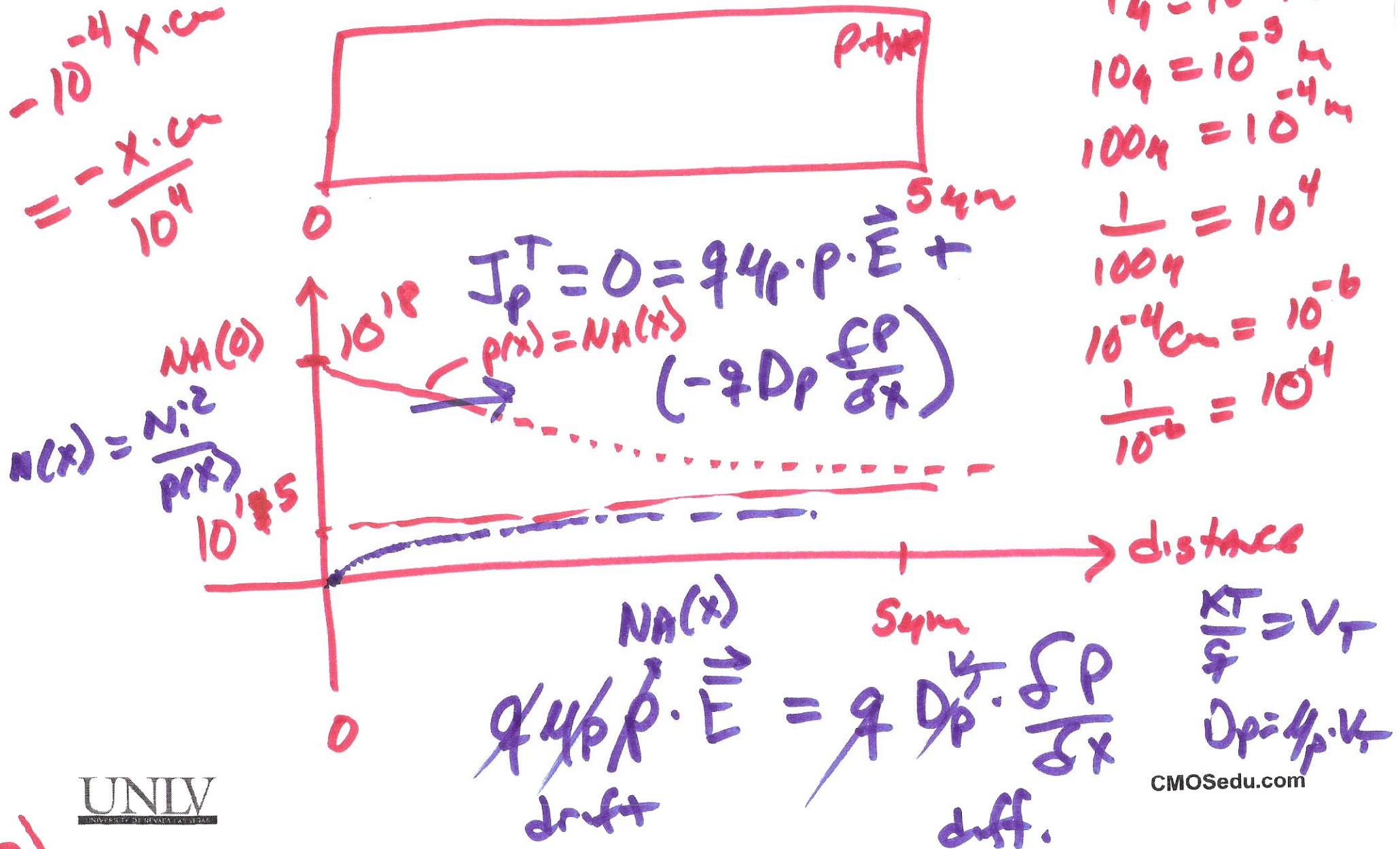
solve for N_{Ai}

$$0.25 \Omega \cdot \text{cm} = \frac{1}{q(\mu_p)(N_{Ai} + N_{AF})}$$

2.51)

$$N_A(x) = 10^{14} + 10^{18} e^{-x/100\mu\text{m}} \quad (2)$$

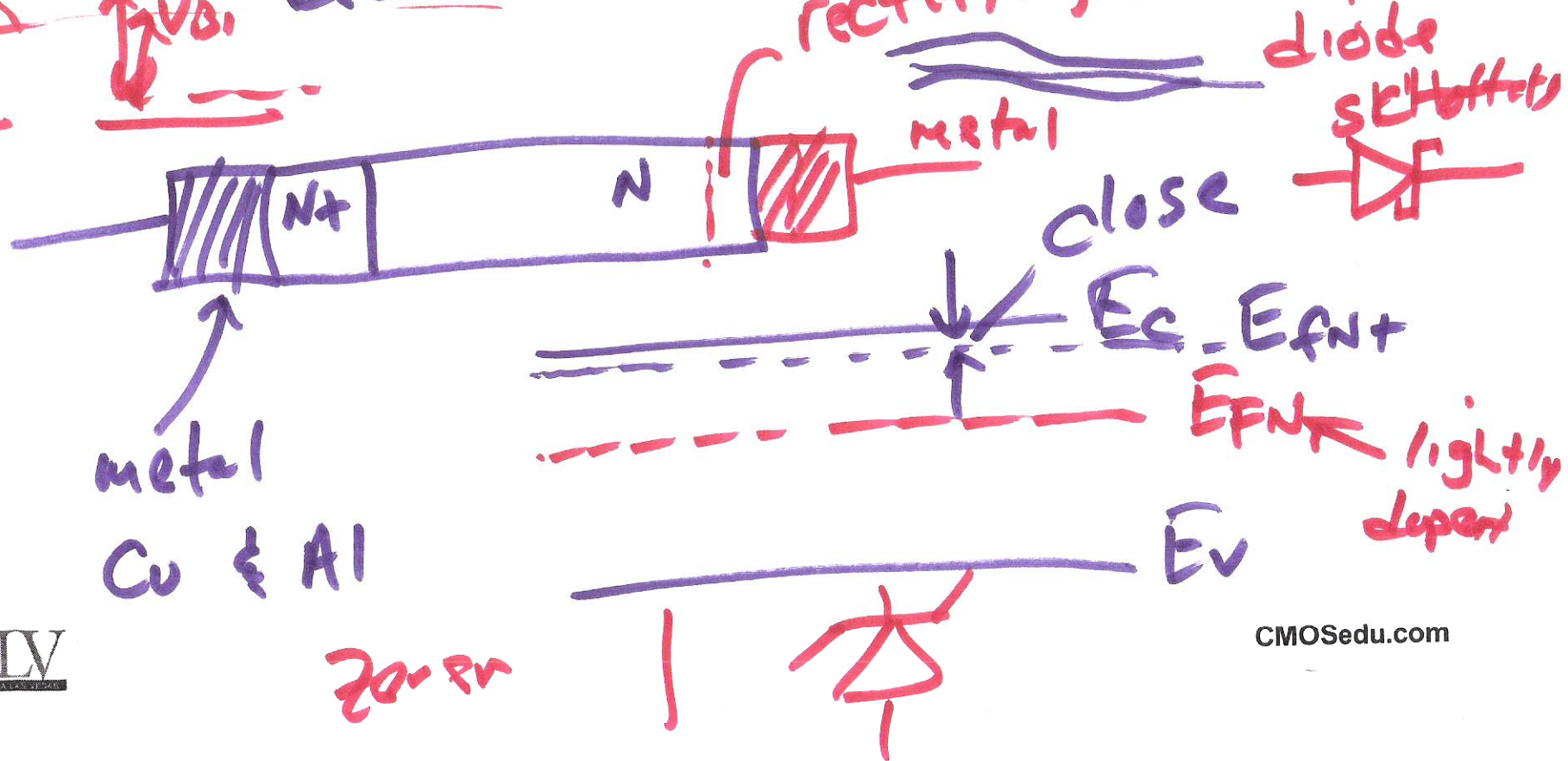
$$-10^{-4} \times \text{cm} = -\frac{x \cdot \text{cm}}{10^4}$$

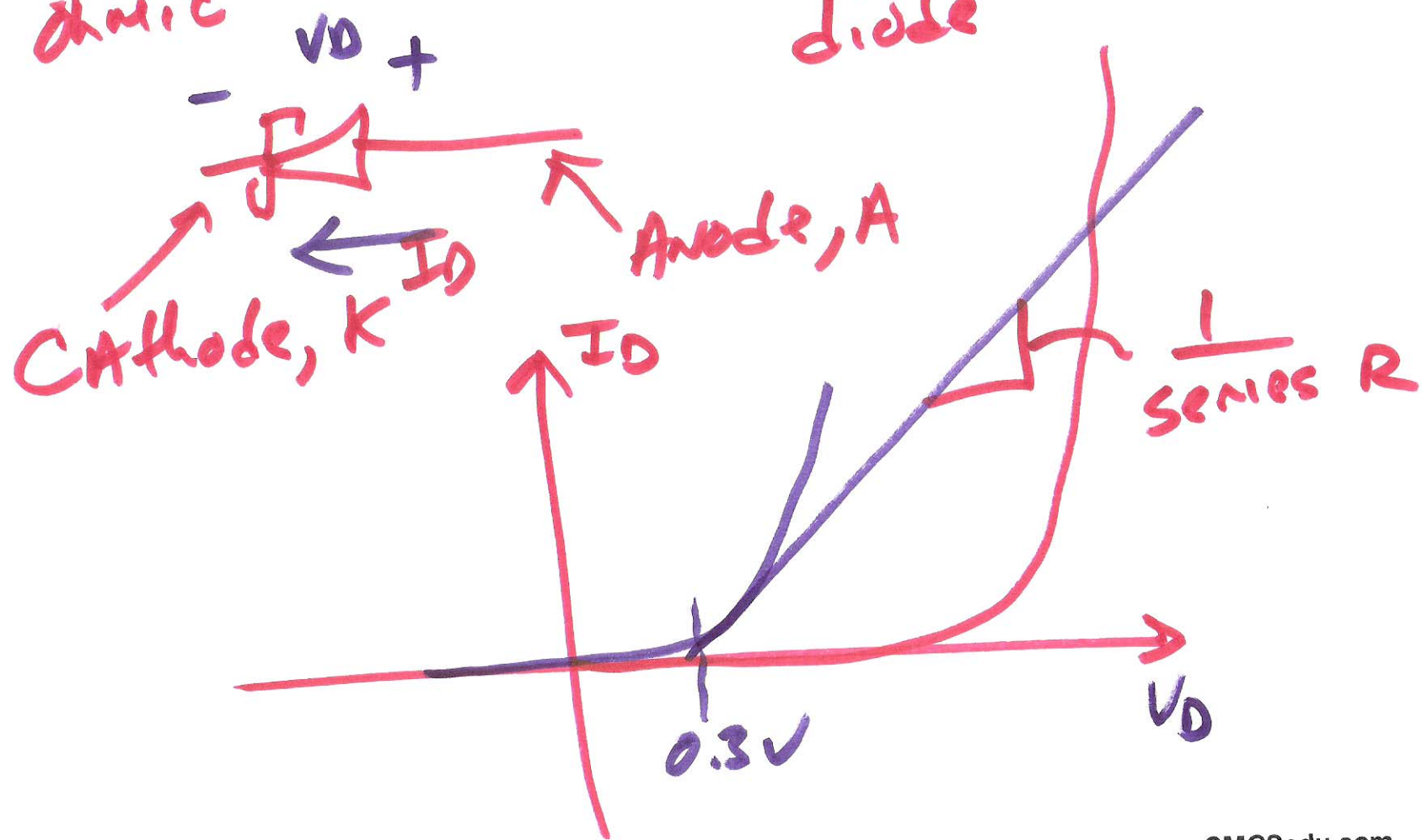
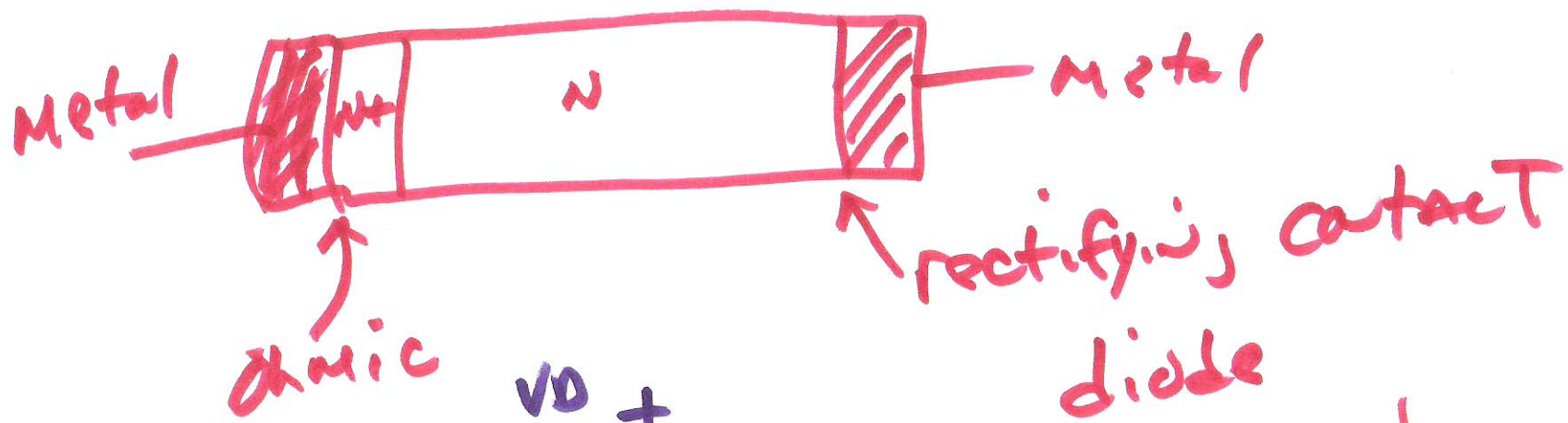


Schottky Diodes

Whenever you connect metal to a semiconductor the semiconductor must be heavily doped.

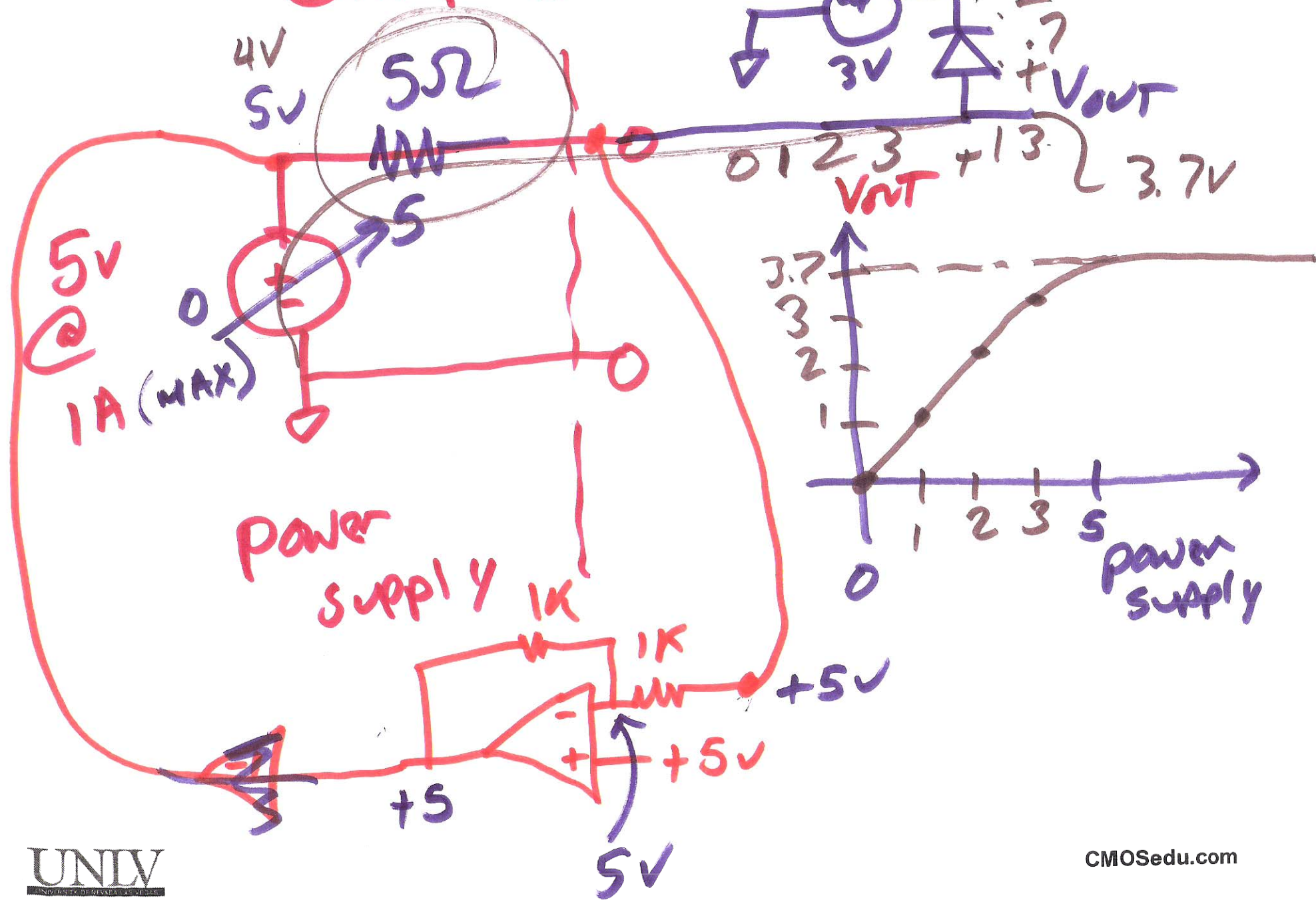
Result is An ohmic contact.
rectifying contact,
diode

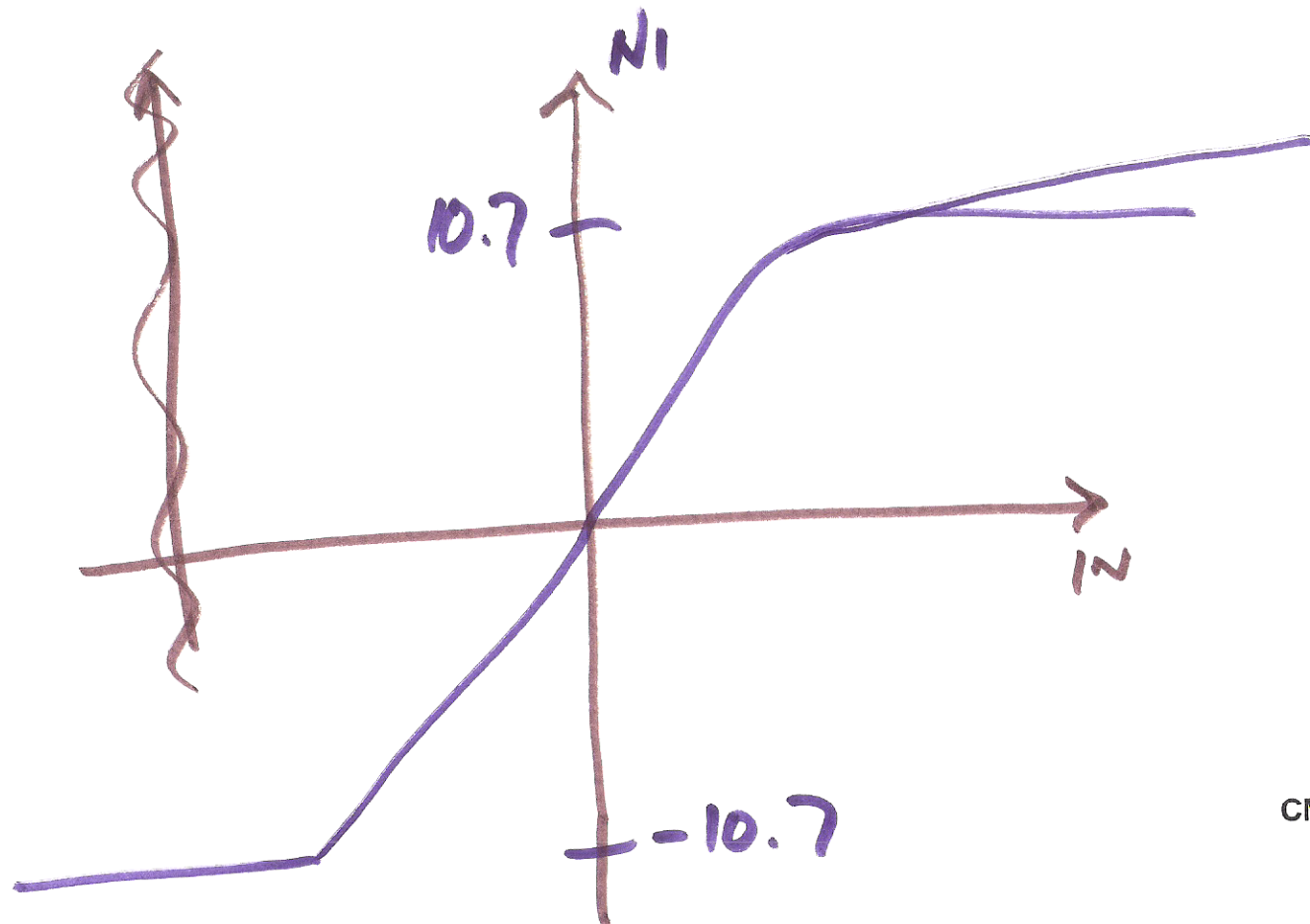
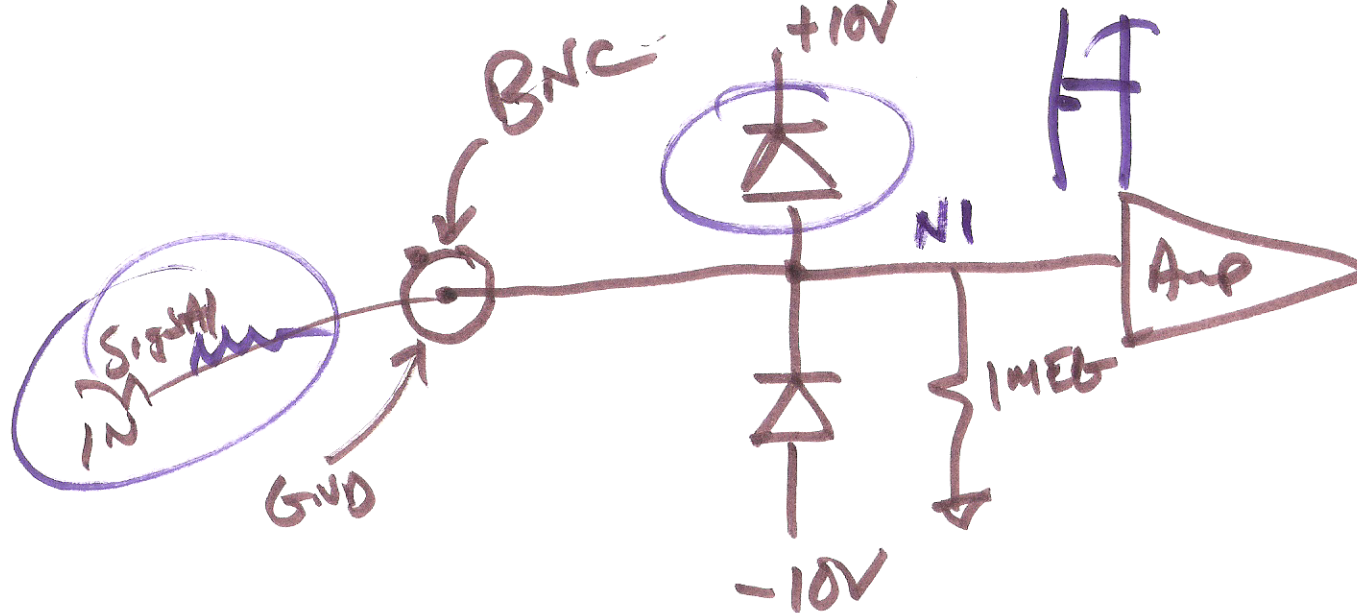




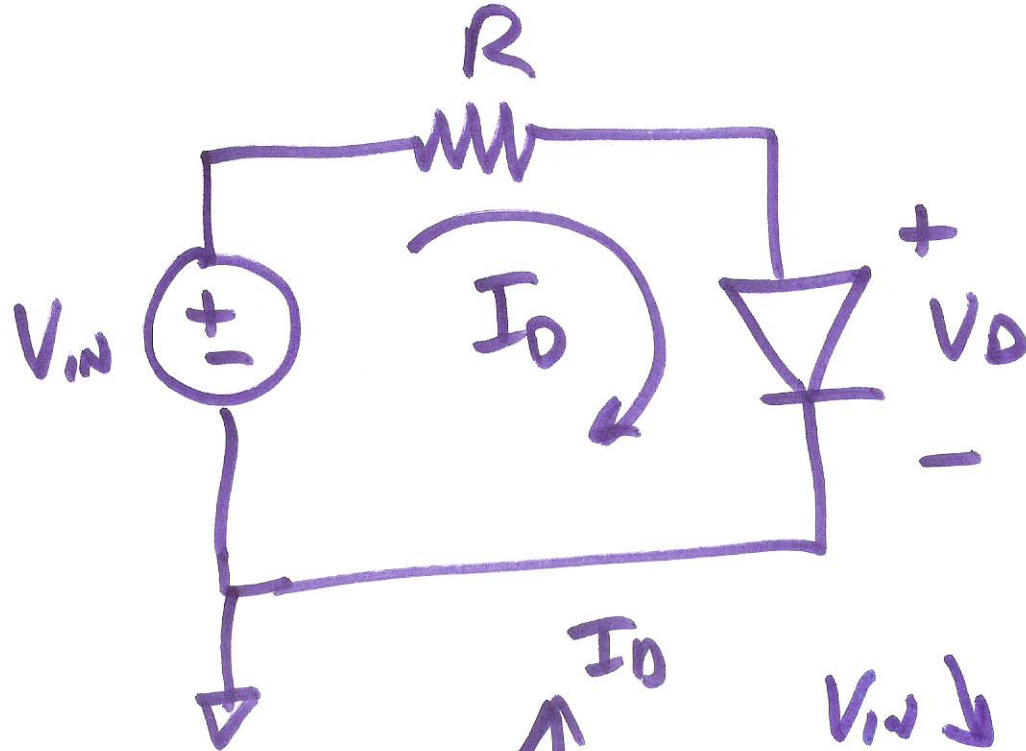
4)

Clamping circuit



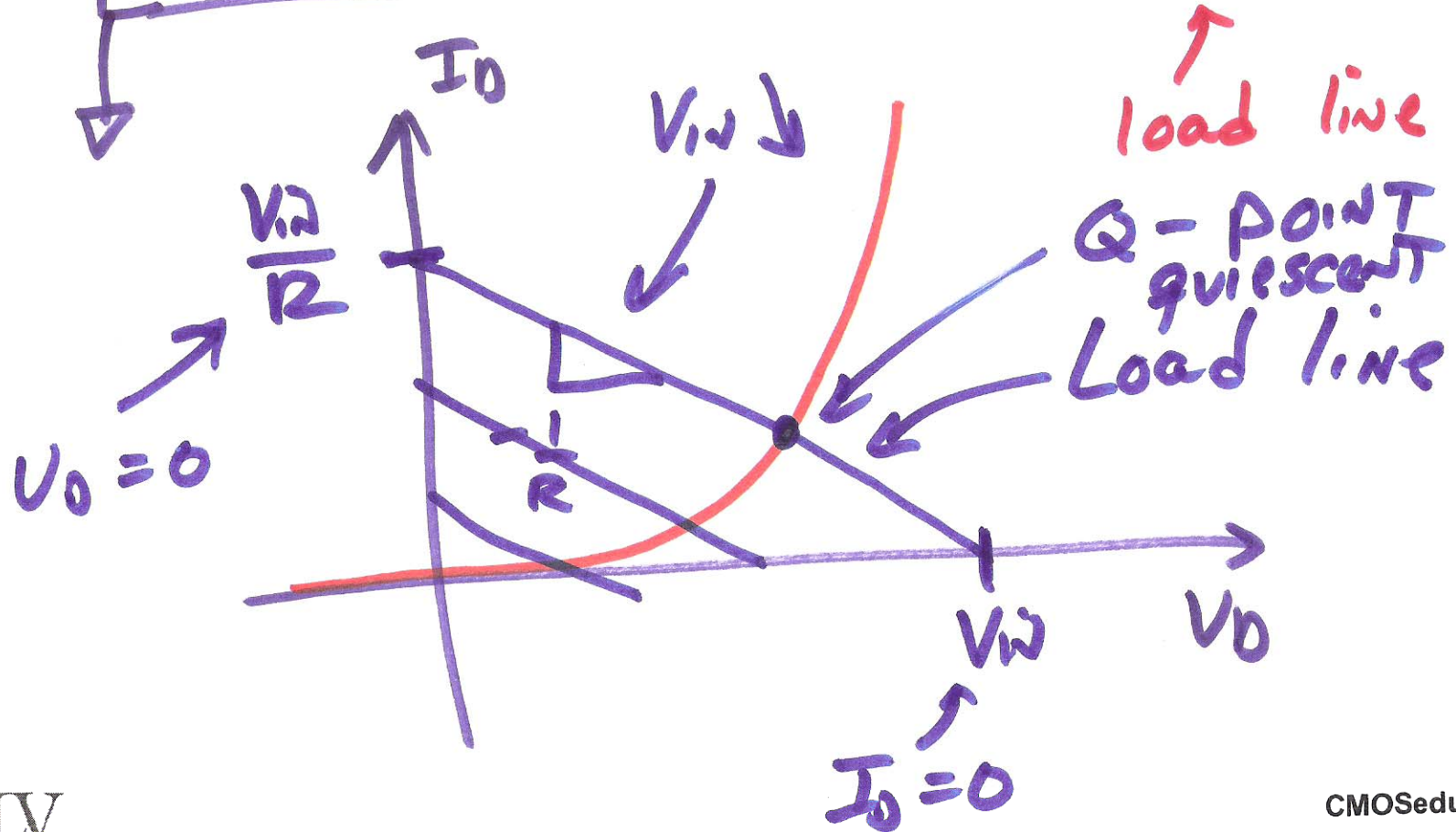


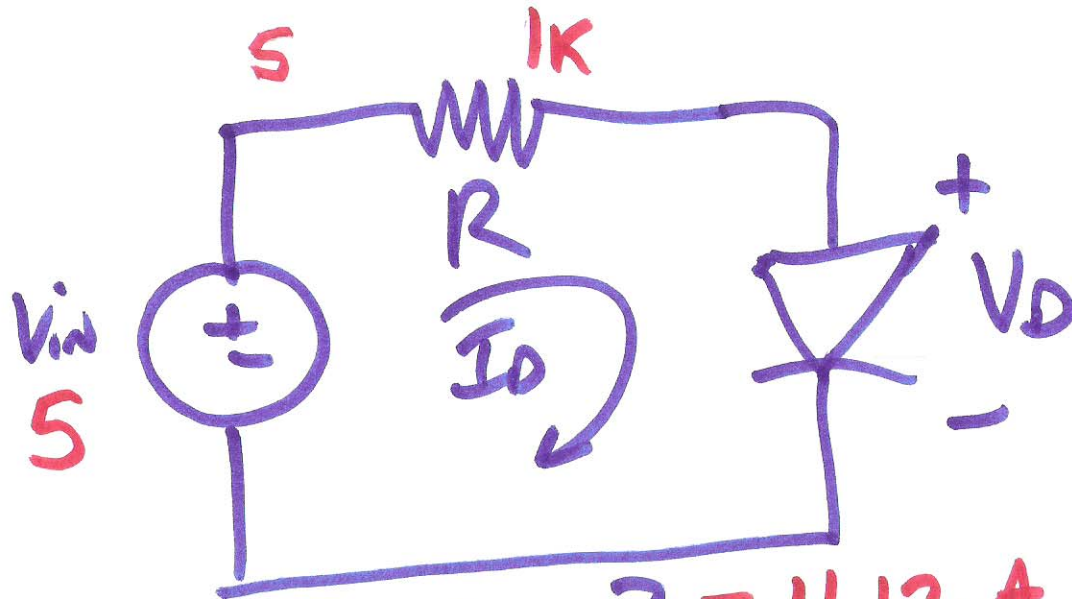
6)



$$I_0 = I = \frac{V_{in} - V_0}{R}$$

$$I_0 = \frac{1}{R} \cdot V_{in} - \frac{V_0}{R}$$





$$I_o = I_s (e^{\frac{V_d}{N V_T}} - 1)$$

for forward bias

$$V_d \approx N V_T \ln \frac{I_o}{I_s}$$

$$I_o = ? = 4.12 \mu A$$

$$V_d = ?$$

$$V_{in} = I_o \cdot R + V_d$$

Left Right

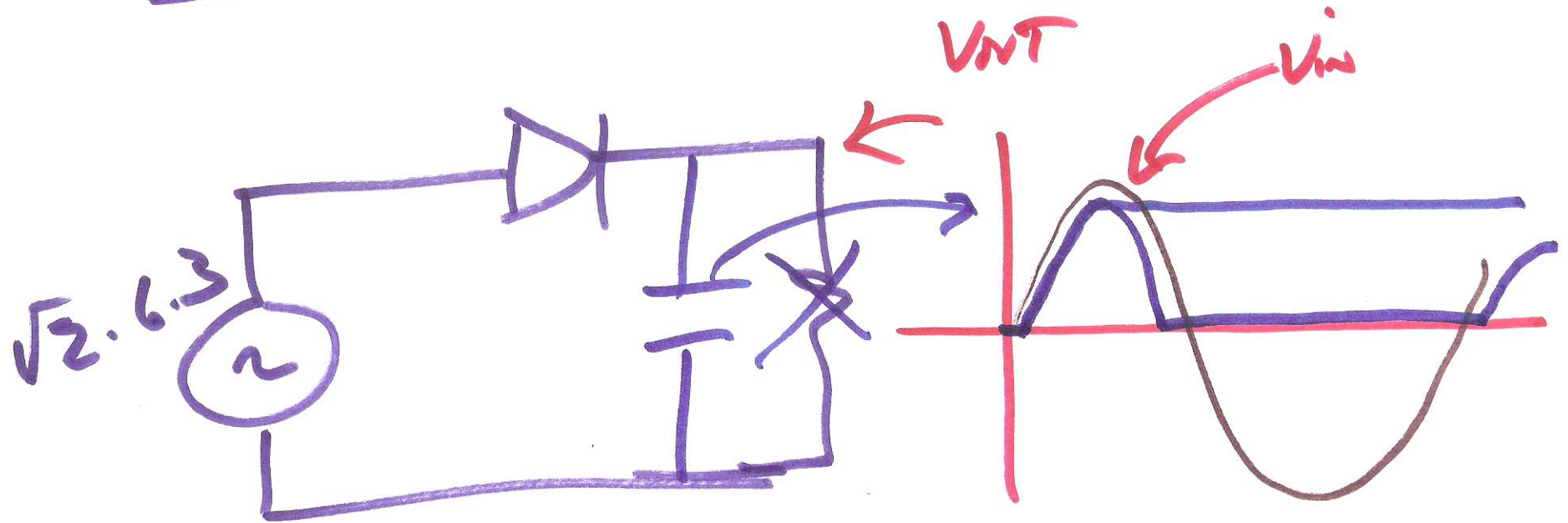
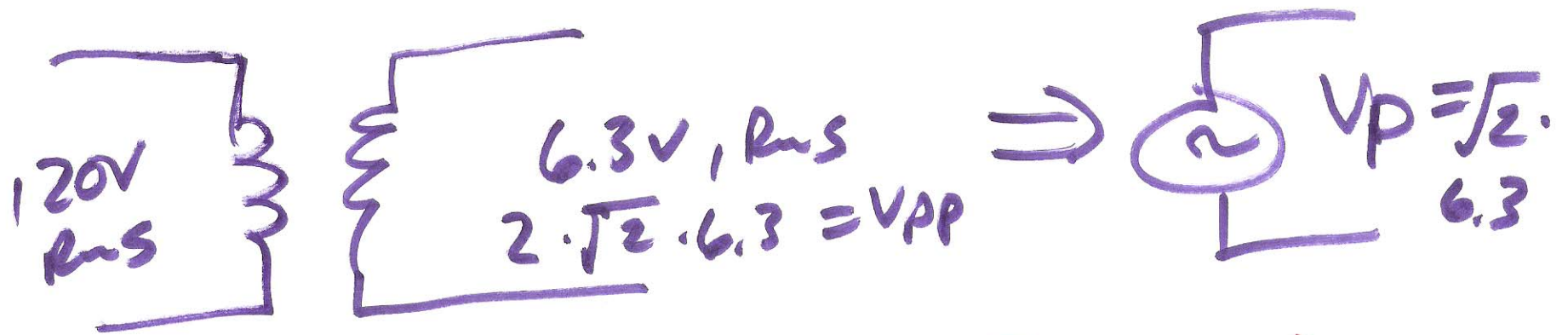
$$V_{in} = I_o \cdot R + N V_T \ln \frac{I_o}{I_s}$$

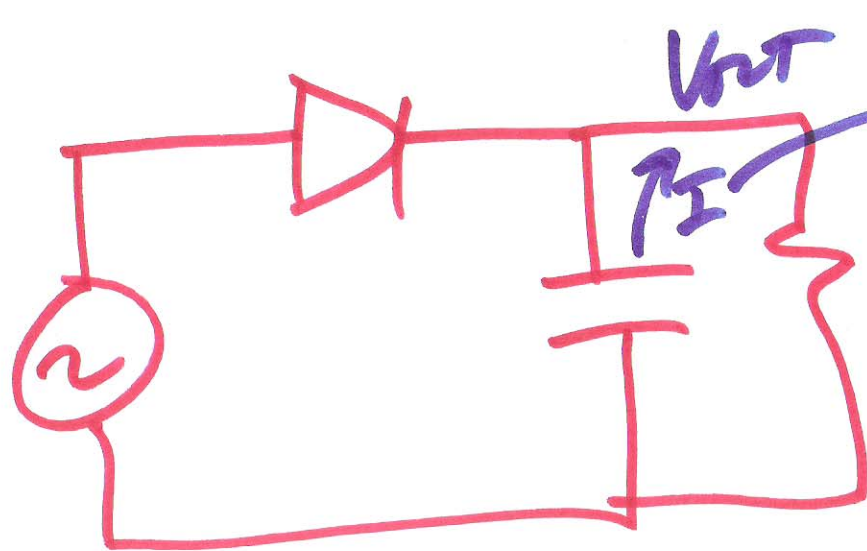
Left Right

$$5 - 4.12 \mu A \cdot 1K = V_d$$

$$= \underline{\underline{.88V}}$$

Left	Right	I_o	D. f.f
		4.3 μA	
		4.12 μA	





$$\frac{V_P}{R} = \text{const current } I$$

$$\text{loop } \Delta Q = \frac{V_P}{R} \cdot T$$

